Silicon Controlled Rectifiers Reverse Blocking Thyristors

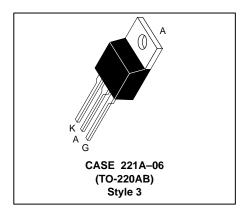
Designed primarily for half-wave ac control applications, such as motor controls, heating controls, and power supplies; or wherever half-wave, silicon gate-controlled devices are needed.

- Blocking Voltage to 800 Volts
- · On-State Current Rating of 25 Amperes RMS
- High Surge Current Capability 300 Amperes
- Industry Standard TO–220AB Package for Ease of Design
- Glass Passivated Junctions for Reliability and Uniformity

MCR25 SERIES

*Motorola preferred devices

SCRs 25 AMPERES RMS 400 thru 800 VOLTS



MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

Parameter		Symbol	Value	Unit
Peak Repetitive Off-State Voltage (1) Peak Repetitive Reverse Voltage (T _J = -40 to 125°C)	MCR25D MCR25M MCR25N	VDRM VRRM	400 600 800	Volts
On-State RMS Current (All Conduction Angles)		I _{T(RMS)}	25	А
Peak Non-repetitive Surge Current (One Half Cycle, 60 Hz, T _J = 125°C)		^I TSM	300	А
Circuit Fusing Consideration (t = 8.3 ms)		l ² t	373	A ² sec
Peak Gate Power (Pulse Width ≤ 1.0 μs, T _C = 80°C)		P _{GM}	20.0	Watts
Average Gate Power (t = 8.3 ms, T _C = 80°C)		P _{G(AV)}	0.5	Watts
Peak Gate Current (Pulse Width ≤ 1.0 μs, T _C = 80°C)		I _{GM}	2.0	А
Operating Junction Temperature Range		TJ	-40 to +125	°C
Storage Temperature Range		T _{stg}	-40 to +150	°C

THERMAL CHARACTERISTICS

Thermal Resistance — Junction to Case — Junction to Ambient	R _θ JC R _θ JA	1.5 62.5	°C/W
Maximum Lead Temperature for Soldering Purposes 1/8" from Case for 5 Seconds	TL	260	°C

⁽¹⁾ V_{DRM} and V_{RRM} for all types can be applied on a continuous basis. Ratings apply for zero or negative gate voltage; positive gate voltage shall not be applied concurrent with negative potential on the anode. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.

Preferred devices are Motorola recommended choices for future use and best overall value. REV 2



MCR25 SERIES

ELECTRICAL CHARACTERISTICS ($T_J = 25^{\circ}C$ unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS					
Peak Forward Blocking Current Peak Reverse Blocking Current $(V_{AK} = Rated \ V_{DRM} \ or \ V_{RRM}, \ Gate \ Open) \qquad \qquad T_{J} = 25^{\circ}C$ $T_{J} = 125^{\circ}C$	I _{DRM} I _{RRM}	_	_	0.01 2.0	mA
ON CHARACTERISTICS					
Peak On-State Voltage* (I _{TM} = 50 A)	V _{TM}	_	_	1.8	Volts
Gate Trigger Current (Continuous dc) ($V_D = 12 \text{ V}, R_L = 100 \Omega$)		4.0	10	30	mA
Gate Trigger Voltage (Continuous dc) ($V_D = 12 \text{ V}, R_L = 100 \Omega$)		0.5	0.65	1.0	Volts
Hold Current (Anode Voltage =12 V)		5.0	25	40	mA
DYNAMIC CHARACTERISTICS					•
Critical Rate of Rise of Off–State Voltage (V _D = Rated V _{DRM} , Exponential Waveform, Gate Open, T _J = 125°C)		50	200	_	V/μs

^{*}Indicates Pulse Test: Pulse Width ≤ 2.0 ms, Duty Cycle ≤ 2%.

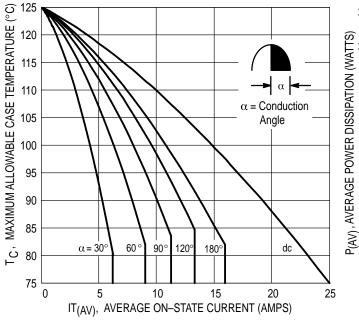


Figure 1. Average Current Derating

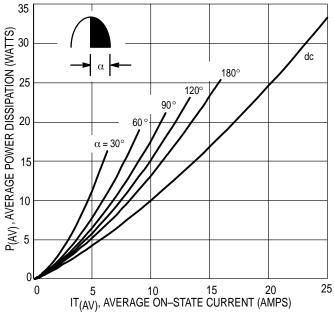


Figure 2. Maximum On-State Power Dissipation

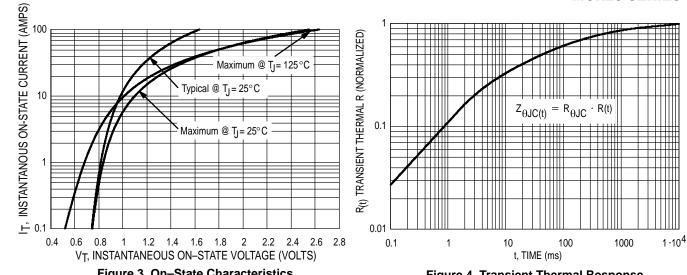


Figure 3. On-State Characteristics



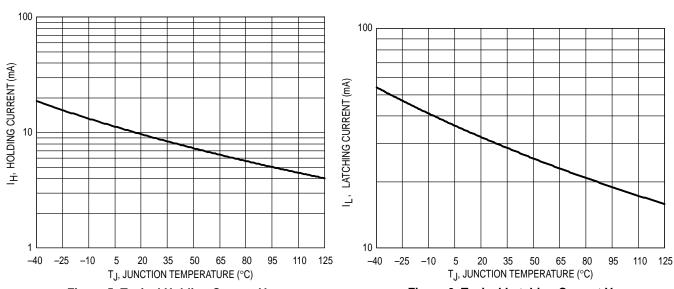


Figure 5. Typical Holding Current Versus **Junction Temperature**

Figure 6. Typical Latching Current Versus **Junction Temperature**

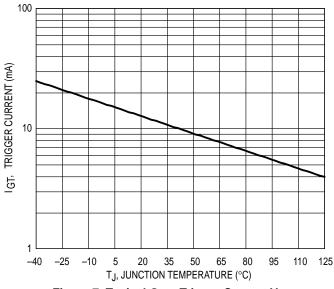


Figure 7. Typical Gate Trigger Current Versus **Junction Temperature**

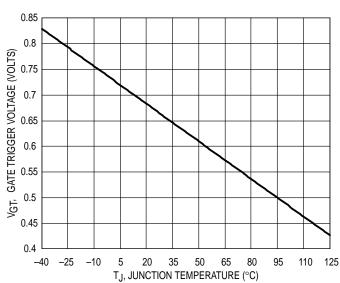


Figure 8. Typical Gate Trigger Voltage Versus **Junction Temperature**

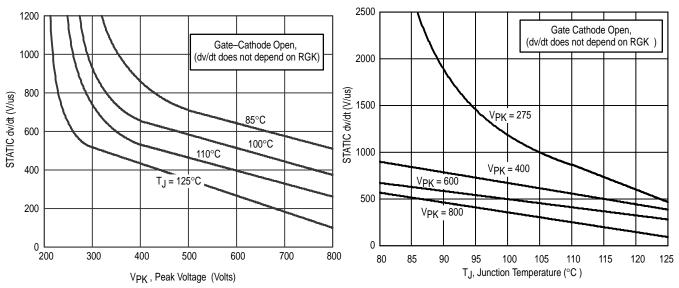


Figure 9. Typical Exponential Static dv/dt Versus Peak Voltage.

Figure 10. Typical Exponential Static dv/dt Versus Junction Temperature.

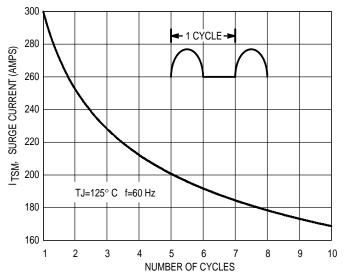
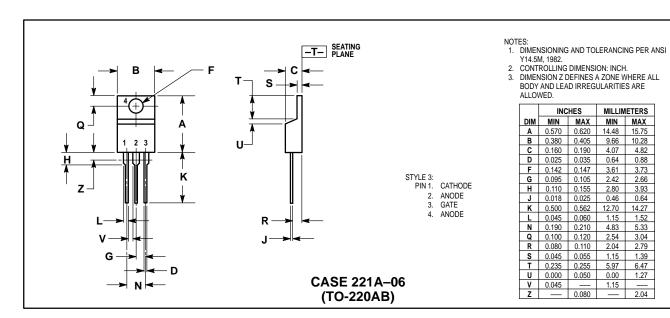


Figure 11. Maximum Non-Repetitive Surge Current

PACKAGE DIMENSIONS



MCR25 SERIES

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